

# P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
	$0.00825$ at $V_{GS} = -4.5 \text{ V}$	- 14		
- 12	0.01025 at V <sub>GS</sub> = - 2.5 V	- 13		
	0.013 at V <sub>GS</sub> = - 1.8 V	- 12		

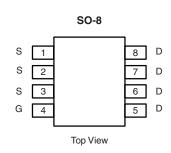
### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



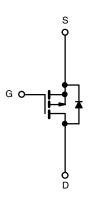
### **APPLICATIONS**

- Load Switch
- · Battery Switch



Ordering Information: Si4451DY-T1-E3 (Lead (Pb)-free)

Si4451DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	T <sub>A</sub> = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	-	12	
Gate-Source Voltage		$V_{GS}$	± 8		V
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	ı	- 14	- 10	•
	T <sub>A</sub> = 70 °C	l <sub>D</sub>	- 11	- 8	
Pulsed Drain Current		I <sub>DM</sub>	- 40		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 2.7	- 1.35	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.0	1.5	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	L D	1.9	0.95	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Manipulation to Applicate	t ≤ 10 s	D	33	42	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	- R <sub>thJA</sub>	70	85	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	17	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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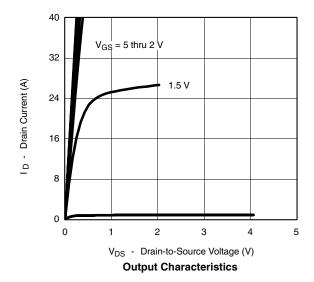
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			1	•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -850 \mu A$	- 0.40		- 0.8	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zara Cata Valtaga Drain Current	l	V <sub>DS</sub> = - 12 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 12 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			- 5	μΑ	
On-State Drain Current <sup>a</sup> I <sub>D(on)</sub> V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 4.5 V		- 30			Α		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 14 A		0.0065	0.00825		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 13 A		0.008	0.01025	-	
	, ,	V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 12 A		0.0105	0.013		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 14 A		55		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 2.7 A, V <sub>GS</sub> = 0 V		- 0.6	- 1.1	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			81	120		
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = -6 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -14 A		8.6		nC	
Gate-Drain Charge	$Q_{gd}$			23.4			
Gate Resistance	$R_g$			3.0		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			55	85		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 6 V, $R_L$ = 6 $\Omega$		125	190		
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong$ - 1 A, $\text{V}_\text{GEN}$ = - 4.5 V, $\text{R}_g$ = 6 $\Omega$		315	480	ns	
Fall Time	t <sub>f</sub>			235	360		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 2.7 A, dl/dt = 100 A/μs		185	300		

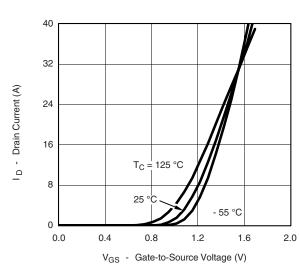
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





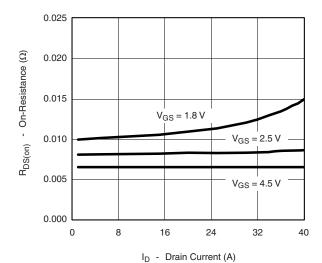
**Transfer Characteristics** 



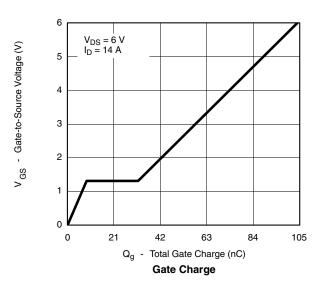


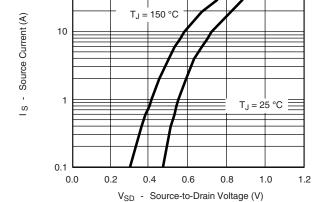


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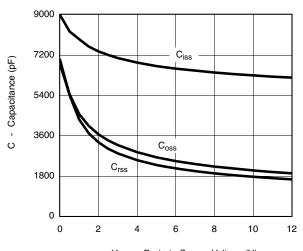


On-Resistance vs. Drain Current



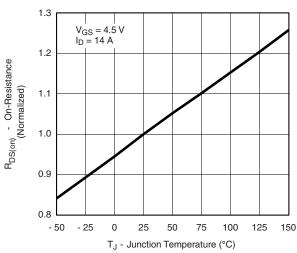


Source-Drain Diode Forward Voltage

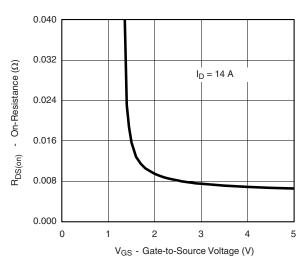


V<sub>DS</sub> - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature



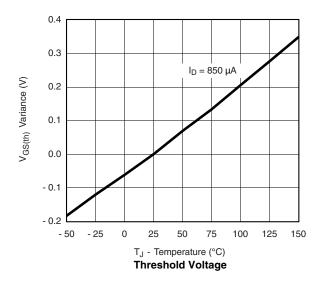
On-Resistance vs. Gate-to-Source Voltage

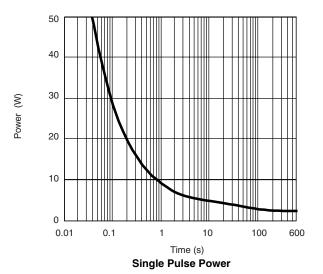
100

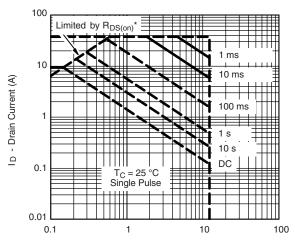
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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

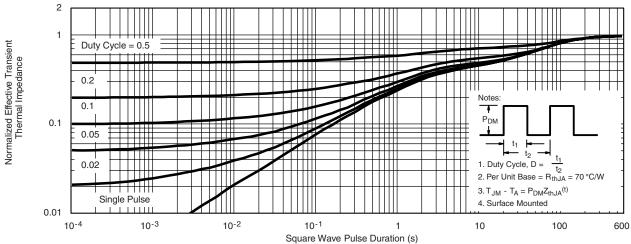






 $V_{DS} \ \, - \ \, \text{Drain-to-Source Voltage (V)} \\ ^* \, V_{GS} > \text{minimum } V_{GS} \, \text{at which } R_{DS(on)} \, \text{is specified}$ 

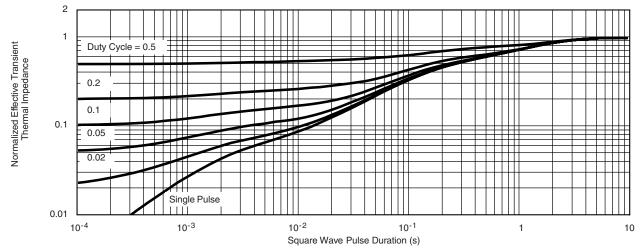
### Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050	0.050 BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
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DWG: 5498

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### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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